**Product data sheet** 

## 1. General description

Power Schottky diode in TO252 (DPAK) surface-mountable plastic package.





## 2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

# 3. Applications

- · DC to DC converters
- · Freewheeling diode
- · OR-ing diode
- · Switched mode power supply rectifier

## 4. Quick reference data

#### Table 1. Quick reference data

| Symbol                 | Parameter                       | Conditions                                                                    | Notes | Values      |      |      | Unit |  |  |  |  |
|------------------------|---------------------------------|-------------------------------------------------------------------------------|-------|-------------|------|------|------|--|--|--|--|
| Absolute               | Absolute maximum rating         |                                                                               |       |             |      |      |      |  |  |  |  |
| $V_{RRM}$              | repetitive peak reverse voltage |                                                                               |       | 100         |      |      | V    |  |  |  |  |
| I <sub>F(AV)</sub>     | average forward current         | $δ = 0.5$ ; square-wave pulse; $T_{mb} \le 125$ °C;<br>Fig. 1; Fig. 2; Fig. 3 |       | 20          |      |      | А    |  |  |  |  |
| Symbol                 | Parameter                       | Conditions                                                                    | Notes | Min Typ Max |      |      | Unit |  |  |  |  |
| Static characteristics |                                 |                                                                               |       |             |      |      |      |  |  |  |  |
| V <sub>F</sub>         | forward voltage                 | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>                  |       | -           | 0.75 | 0.85 | V    |  |  |  |  |
| I <sub>R</sub>         | reverse current                 | V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C                                |       | -           | 15   | 50   | μA   |  |  |  |  |

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol      |
|-----|--------|-------------------------------------|--------------------|---------------------|
| 1   | А      | anode                               |                    | K A                 |
| 2   | K      | cathode                             |                    | K —— A<br>001aaa020 |
| 3   | А      | anode                               |                    |                     |
| mb  | К      | mounting base; connected to cathode |                    |                     |
|     |        |                                     |                    |                     |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WN3S20100D  | TO252        | WN3S20100DJ           | Reel           | 2500                   | TO252d          | 07-Sep-2022        |

## 7. Marking

#### Table 4. Marking codes

| Type number | Marking codes  |
|-------------|----------------|
| WN3S20100D  | WN3S20<br>100D |

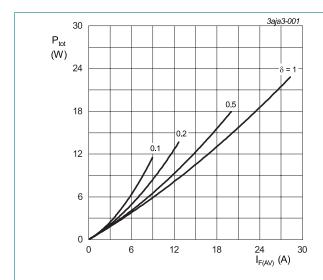
# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

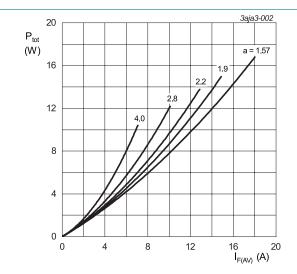
| Symbol             | Parameter                           | Conditions                                                                             | Notes | Values     | Unit |
|--------------------|-------------------------------------|----------------------------------------------------------------------------------------|-------|------------|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |                                                                                        |       | 100        | V    |
| $V_{\text{RWM}}$   | crest working reverse voltage       |                                                                                        |       | 100        | V    |
| $V_R$              | reverse voltage                     | DC                                                                                     |       | 100        | V    |
| I <sub>F(AV)</sub> | average forward current             | $\delta$ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 125 °C;<br>Fig. 1; Fig. 2; Fig. 3 |       | 20         | A    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4                       |       | 250        | А    |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                                 |       | 275        | Α    |
| T <sub>stg</sub>   | storage temperature                 |                                                                                        |       | -40 to 150 | °C   |
| T <sub>j</sub>     | junction temperature                |                                                                                        | [1]   | -40 to 150 | °C   |

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$ 



$$\begin{split} &I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta} \\ &V_o = 0.584 \text{ V; } R_s = 0.0078 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}$  /  $I_{F(AV)}$  V<sub>o</sub> = 0.584 V; R<sub>s</sub> = 0.0078  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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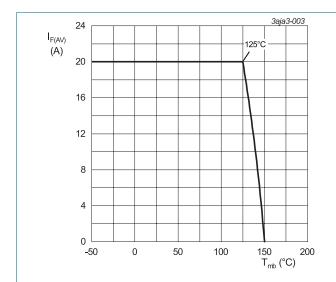


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

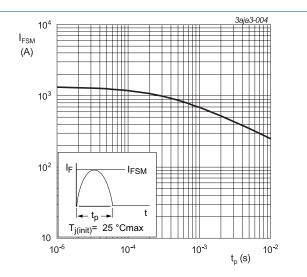


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter                                               | Conditions    | Notes | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------------------------|---------------|-------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | <u>Fig. 5</u> |       | -   | -   | 1.4 | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient       | in free air   |       | -   | 50  | -   | K/W  |

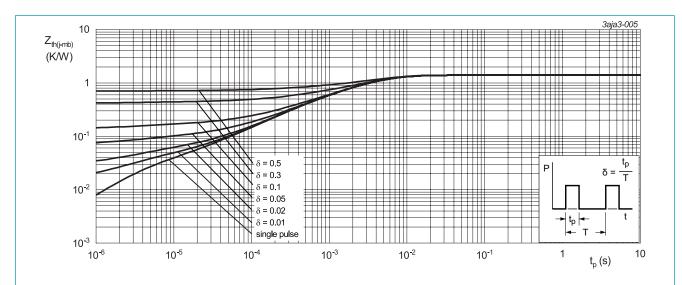
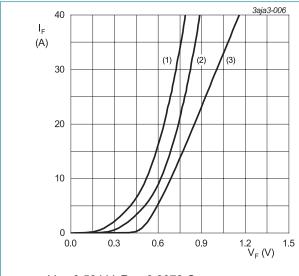


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

## 10. Characteristics

**Table 7. Characteristics** 

| Symbol         | Parameter       | Conditions                                                                     | Notes | Min | Тур  | Max  | Unit |
|----------------|-----------------|--------------------------------------------------------------------------------|-------|-----|------|------|------|
| Static ch      | aracteristics   |                                                                                |       |     |      |      |      |
| V <sub>F</sub> | forward voltage | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>                   |       | -   | 0.75 | 0.85 | V    |
|                |                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>                   |       | -   | 0.59 | -    | V    |
|                |                 | I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>                    |       | -   | 0.45 | -    | V    |
|                |                 | I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>                  |       | -   | 0.68 | -    | V    |
|                |                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>                  |       | -   | 0.55 | -    | V    |
|                |                 | I <sub>F</sub> = 3 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>                   |       | -   | 0.37 | -    | V    |
| I <sub>R</sub> | reverse current | V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C; <u>Fig. 7</u> ; <u>Fig. 8</u>  |       | -   | 15   | 50   | μΑ   |
|                |                 | V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; <u>Fig. 7</u> ; <u>Fig. 8</u> |       | -   | 7    | 30   | mA   |

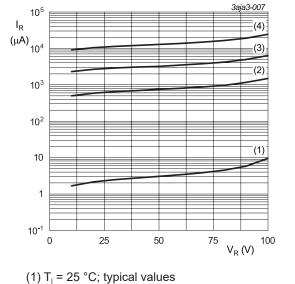


 $V_o$  = 0.584 V;  $R_s$  = 0.0078  $\Omega$ 

(1) T<sub>j</sub> = 150 °C; typical values

(2) T<sub>j</sub> = 150 °C; maximum values (3) T<sub>j</sub> = 25 °C; maximum values

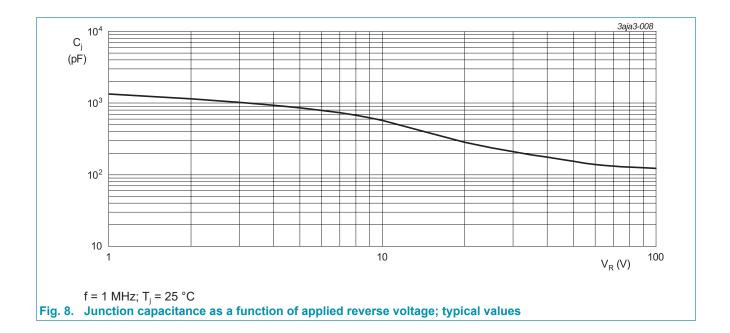
Fig. 6. Forward current as a function of forward voltage



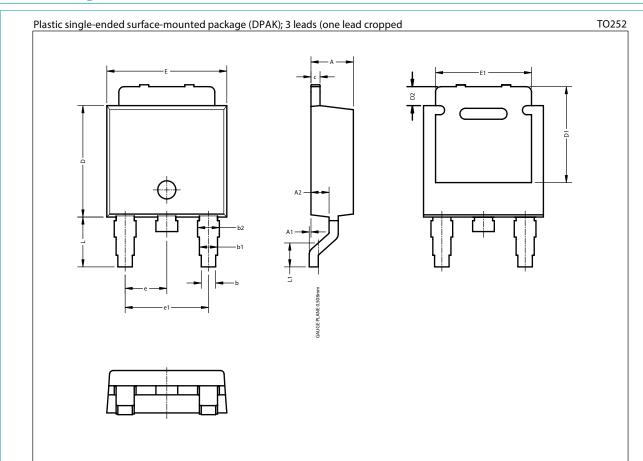
(2) T<sub>j</sub> = 100 °C; typical values

(3)  $T_j = 125$  °C; typical values (4)  $T_j = 150$  °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; typical values



# 11. Package outline



#### Note:

1. All dimensions do not include mold flash & gate remain and metal protrusion.

| Unit          | Α | <b>A</b> 1 | <b>A2</b> | b    | b1   | b2   | С    | D    | D1   | D2   | E    | E1   | е    | e1   | L    | L1   |
|---------------|---|------------|-----------|------|------|------|------|------|------|------|------|------|------|------|------|------|
| min<br>mm nom | 1 | 0.00       | 0.90      | 0.70 | 0.86 | 1.06 | 0.46 | 5.97 | 5.05 | 0.98 | 6.45 | 5.20 | 2.30 | 4.60 | 2.60 | 1.25 |
|               | 1 | 0.10       | 1.10      | 0.90 | 1.11 | 1.32 | 0.58 | 6.22 | 5.35 | 1.18 | 6.75 | 5.40 |      |      | 2.90 | 1.65 |

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#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition                                                                            |
|--------------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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WN3S20100D

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